

MH185 Hall-effect sensor is a temperature stable, stress-resistant sensor. Superior high-temperature performance is made possible through a dynamic offset cancellation that utilizes chopper-stabilization. This method reduces the offset voltage normally caused by device over molding, temperature dependencies, and thermal stress.

MH185 includes the following on a single silicon chip: voltage regulator, Hall voltage generator, small-signal amplifier, chopper stabilization, Schmitt trigger, and open drain output. Advanced DMOS wafer fabrication processing is used to take advantage of low-voltage requirements, component matching, very low input-offset errors, and small component geometries.

This device requires the presence of both south and north polarity magnetic fields for operation. In the presence of a south polarity field of sufficient strength, the device output sensor on, and only switches off when a north polarity field of sufficient strength is present.

MH185 is rated for operation between the ambient temperatures -40°C and 85°C for the E temperature range, and -40°C to 125°C for the K temperature range. The package style available provide magnetically optimized solutions for most applications. Package SO is an SOT-23, a miniature low-profile surface-mount package.

Packages is Halogen Free standard and which have been verified by third party lab.


Features and Benefits

- DMOS Hall IC Technology
- Chopper stabilized amplifier stage.
- Optimized for BLDC motor applications.
- Reliable and low shifting on high Temp condition.
- Switching offset compensation at typically 69kHz
- Good ESD Protection.
- 100% tested at 125°C for K.
- Custom sensitivity / Temperature selection are available.
- Reverse bias protection on power supply pin.
- RoHS compliant 2011/65/EU and Halogen Free

Applications

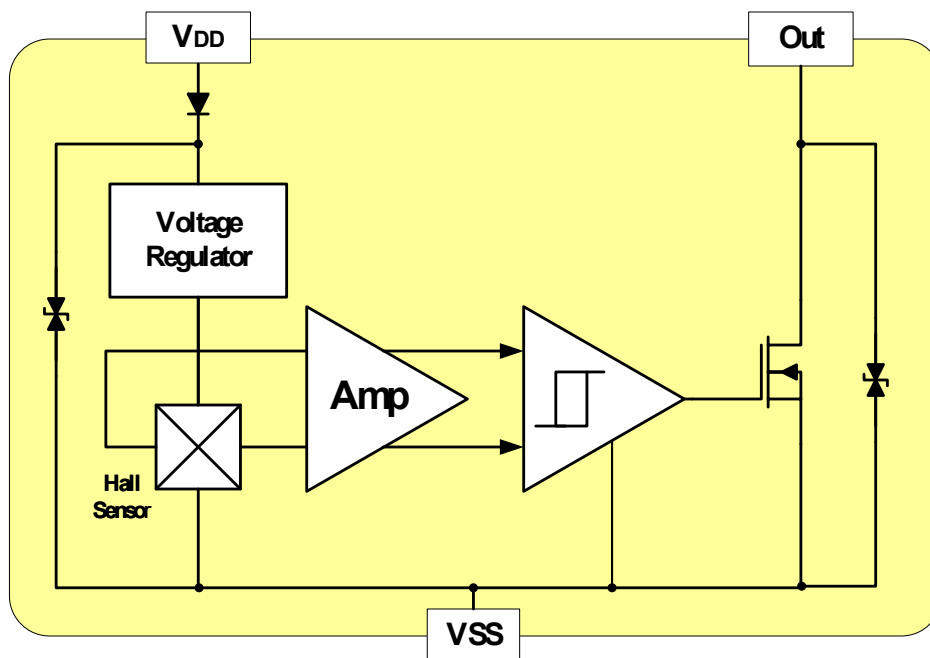
- High temperature Fan motor
- 3 phase BLDC motor application
- Speed sensing
- Position sensing
- Current sensing
- Revolution counting
- Solid-State Switch
- Linear Position Detection
- Angular Position Detection
- Proximity Detection
- High ESD Capability

Ordering Information

	<p>Company Name and Product Category MH:MST Hall Effect/MP:MST Power MOSFET</p> <p>Part number 181,182,183,184,185,248,249,276,477,381,381F,381R,382..... If part # is just 3 digits, the forth digit will be omitted.</p> <p>Temperature range E: 85 °C, I: 105 °C, K: 125 °C, L: 150 °C</p> <p>Package type UA:TO-92S,VK:TO-92S(4pin),VF:TO-92S(5pin),SO:SOT-23, SQ:QFN-3,ST:TSOT-23,SN:SOT-553,SF:SOT-89(5pin)</p> <p>Sorting α,β,Blank.....</p>
<p>Sorting Code</p> <p>Package type</p> <p>Temperature Code</p> <p>Part number</p> <p>Company Name and product Category</p>	

Part No.	Temperature Suffix	Package Type
MH185KSO	K (-40°C to + 125°C)	SO (SOT-23)

Functional Diagram



Absolute Maximum Ratings At ($T_a=25^{\circ}\text{C}$)

Characteristics	Values	Unit	
Supply voltage, (V_{DD})	28	V	
Output Voltage, (V_{out})	28	V	
Reverse Voltage, (V_{DD} / V_{out})	-0.3	V	
Output current, (I_{SINK})	25	mA	
Operating Temperature Range, (T_A)	“E” Class	-40 ~ +85	$^{\circ}\text{C}$
	“K” Class	-40 ~ +125	$^{\circ}\text{C}$
Storage temperature range, (T_S)	-65 to +150	$^{\circ}\text{C}$	
Maximum Junction Temp, (T_J)	150	$^{\circ}\text{C}$	
Thermal Resistance	(θ_{JA}) SO	543	$^{\circ}\text{C}/\text{W}$
	(θ_{JC}) SO	410	$^{\circ}\text{C}/\text{W}$
Package Power Dissipation, (P_D) SO	230	mW	

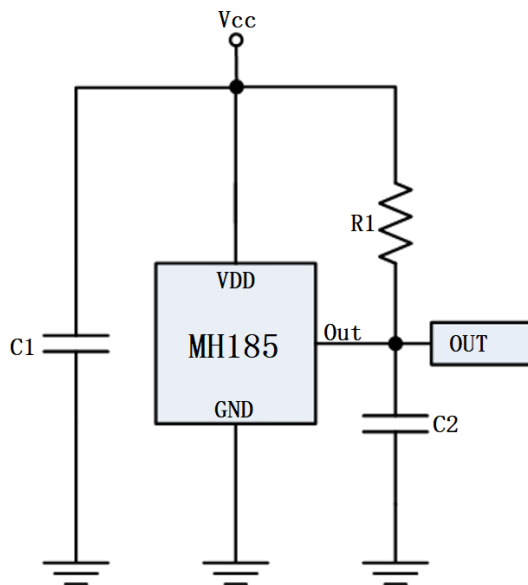
Note: Do not apply reverse voltage to V_{DD} and V_{OUT} Pin, It may be caused for Miss function or damaged device.

Electrical Specifications

DC Operating Parameters : $T_A=+25^{\circ}\text{C}$, $V_{DD}=12\text{V}$

Parameters	Test Conditions	Min	Typ	Max	Units
Supply Voltage, (V_{DD})	Operating	2.5		26	V
Supply Current, (I_{DD})	$B < B_{OP}$		3.0	5.0	mA
Output Saturation Voltage, (V_{sat})	$B > B_{OP}$			400.0	mV
Output Leakage Current, (I_{off})	$I_{OFF} B < B_{RP}$, $V_{OUT} = 12\text{V}$			10.0	μA
Output Rise Time, (T_R)	$R_L=1.1\text{K}\Omega$, $C_L=20\text{pF}$			0.45	μS
Output Fall Time, (T_F)	$R_L=820\Omega$; $C_L=20\text{pF}$			0.45	μS
Electro-Static Discharge	HBM	4			KV
Operate Point, (B_{OP})	SO	5		60	GS
Release Point, (B_{RP})	SO	-60		-5	GS
Hysteresis, (B_{HYS})	$ B_{OP} - B_{RP} $		60		GS

Typical application circuit



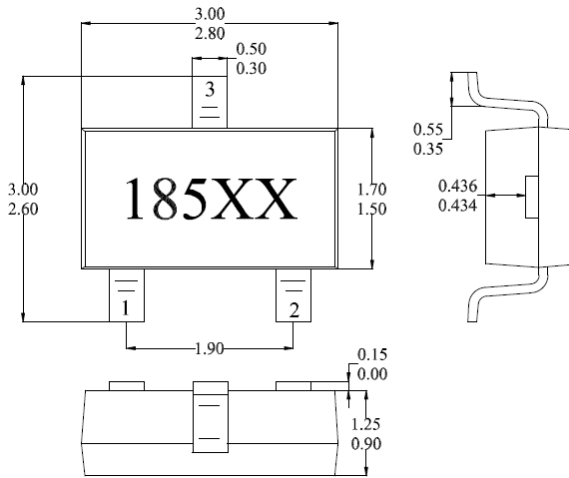
$C1 : 10\text{nF}$

$C2 : 1\text{nF}$

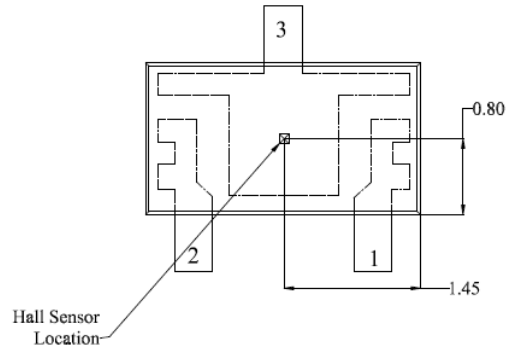
$R1 : 1\text{K}\Omega$

Sensor Location, Package Dimension and Marking

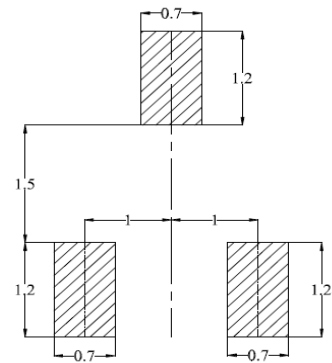
**SO Package
(Top View)**



**Hall Plate Chip Location
(Bottom view)**



(For reference only) Land Pattern



NOTES:

1. PINOUT (See Top View at left :)
 Pin 1 V_{DD}
 Pin 2 Output
 Pin 3 GND
2. Controlling dimension: mm
3. Lead thickness after solder plating will be 0.254mm maximum